Product data sheet

1. General description

P-channel enhancement mode MOSFET in an LFPAK56 (Power SO8) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

This product has been designed and qualified to AEC-Q101 standard for use in high-performance automotive applications such as reverse battery protection.

2. Features and benefits

- · High thermal power dissipation capability
- Suitable for thermally demanding environments due to 175 °C rating
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- · Reverse battery protection
- · Power management
- · High-side loadswitch
- Motor drive

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-40	V
V_{GS}	gate-source voltage		[1]	-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{mb} = 25 °C		-	-	-63	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C		-	-	106	W
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -11 A; T_j = 25 °C		-	11	15	mΩ

[1] V_{GS} = -20 V/+5 V according AEC-Q101 at T_j = 175 °C; V_{GS} = -20 V/+20 V according AEC-Q101 at T_j = 150 °C



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
3	S	source		G P
4	G	gate		s
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	017aaa094

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK6Y15-40P	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK6Y15-40P	6Y1540P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-40	V
V _{GS}	gate-source voltage		[1]	-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{mb} = 25 °C		-	-63	Α
		V _{GS} = -10 V; T _{mb} = 100 °C		-	-45	Α
I _{DM}	peak drain current	single pulse; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$		-	-252	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C		-	106	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C		-	-63	Α
I _{SM}	peak source current	single pulse; $t_p \le 10 \mu s$; $T_{mb} = 25 \degree C$		-	-252	Α
ESD maximu	ım rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	1000	V
Avalanche ru	uggedness			'	<u>'</u>	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$V_{sup} \le -40 \text{ V}; V_{GS} = -10 \text{ V}; T_{j(init)} = 25 ^{\circ}\text{C};$ $I_D = -10.8 \text{ A}; DUT in avalanche}$ (unclamped)		-	5.8	mJ

^[1] V_{GS} = -20 V/+5 V according AEC-Q101 at T_j = 175 °C; V_{GS} = -20 V/+20 V according AEC-Q101 at T_j = 150 °C

^[2] Measured between all pins.

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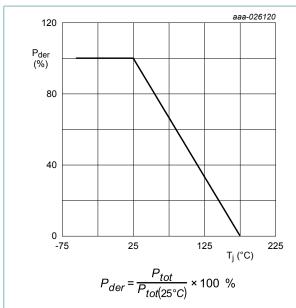


Fig. 1. Normalized total power dissipation as a function of junction temperature

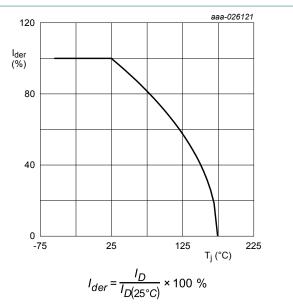


Fig. 2. Normalized continuous drain current as a function of junction temperature

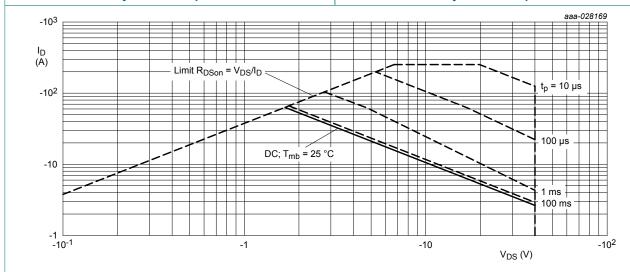


Fig. 3. Safe operating area; junction to mounting base; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	1.1	1.4	K/W

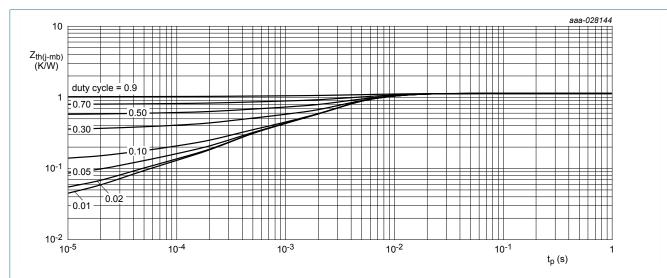


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics $T_{i} = 25 \,^{\circ}\text{C unless otherwise specified}$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics				'	
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V$	-40	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$	-1.5	-2	-3	V
I _{DSS}	drain leakage current	V _{DS} = -40 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{DS} = -40 V; V _{GS} = 0 V; T _j = 175 °C	-	-	-50	μΑ
I _{GSS} g	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = -10 V; I _D = -11 A; T _j = 25 °C	-	11	15	mΩ
	resistance	V _{GS} = -10 V; I _D = -11 A; T _j = 175 °C	-	19	27	mΩ
		V _{GS} = -4.5 V; I _D = -8.4 A	-	16	24	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -2 A; T_j = 25 °C	-	55	-	S
R _G	gate resistance	f = 1 MHz	-	6.8	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -20 V; I_{D} = -10 A; V_{GS} = -10 V	-	43.5	50	nC
Q _{GS}	gate-source charge		-	7.9	-	nC
Q_{GD}	gate-drain charge	-	-	9.2	-	nC
C _{iss}	input capacitance	V _{DS} = -20 V; f = 1 MHz; V _{GS} = 0 V	-	2470	-	pF
C _{oss}	output capacitance		-	330	-	pF
C _{rss}	reverse transfer capacitance		-	199	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -20 V; I _D = -11 A; V _{GS} = -10 V;	-	9	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$	-	31	-	ns
t _{d(off)}	turn-off delay time]	-	71	-	ns
t _f	fall time	1	-	37	-	ns
Source-drai	n diode		1			
V _{SD}	source-drain voltage	$I_S = -63 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V
t _{rr}	reverse recovery time	I_S = -11 A; dI_S/dt = 100 A/ μ s; V_{GS} = 0 V; V_{DS} = -20 V; T_i = 25 °C	-	32	-	ns

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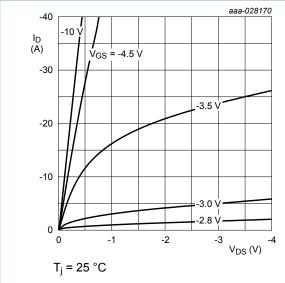


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

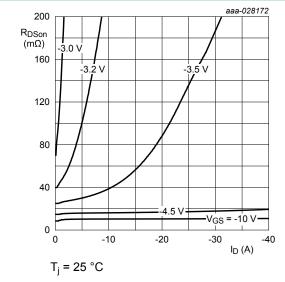


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

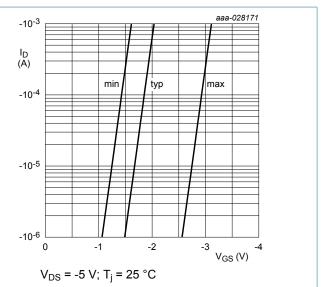


Fig. 6. Sub-threshold drain current as a function of gate-source voltage

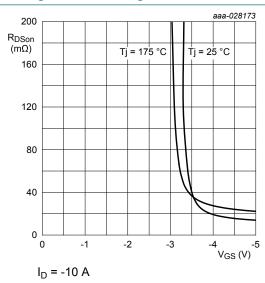


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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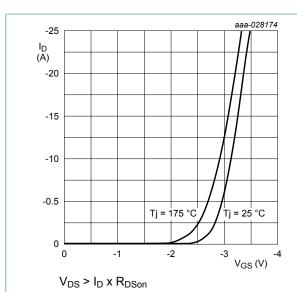


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

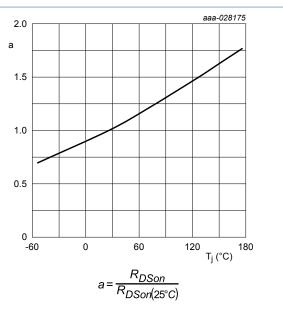


Fig. 10. Normalized drain-source on-state resistance as a function of junction temperature; typical values

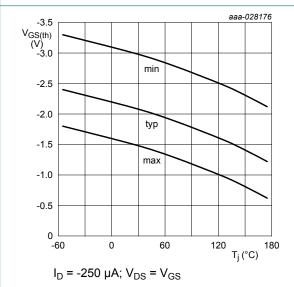


Fig. 11. Gate-source threshold voltage as a function of junction temperature

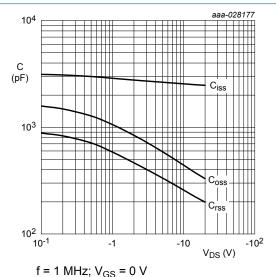


Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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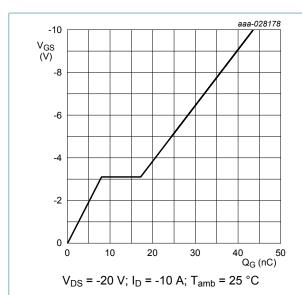


Fig. 13. Gate-source voltage as a function of gate charge; typical values

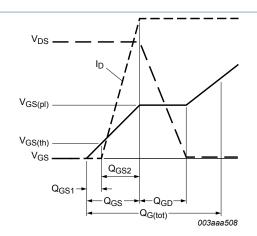


Fig. 14. Gate charge waveform definitions

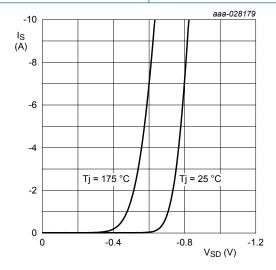
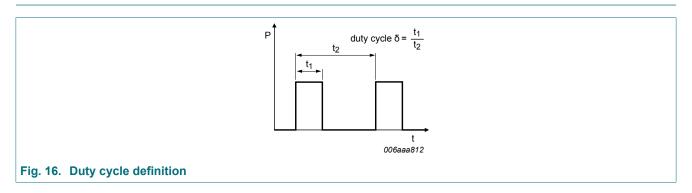


Fig. 15. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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11. Test information

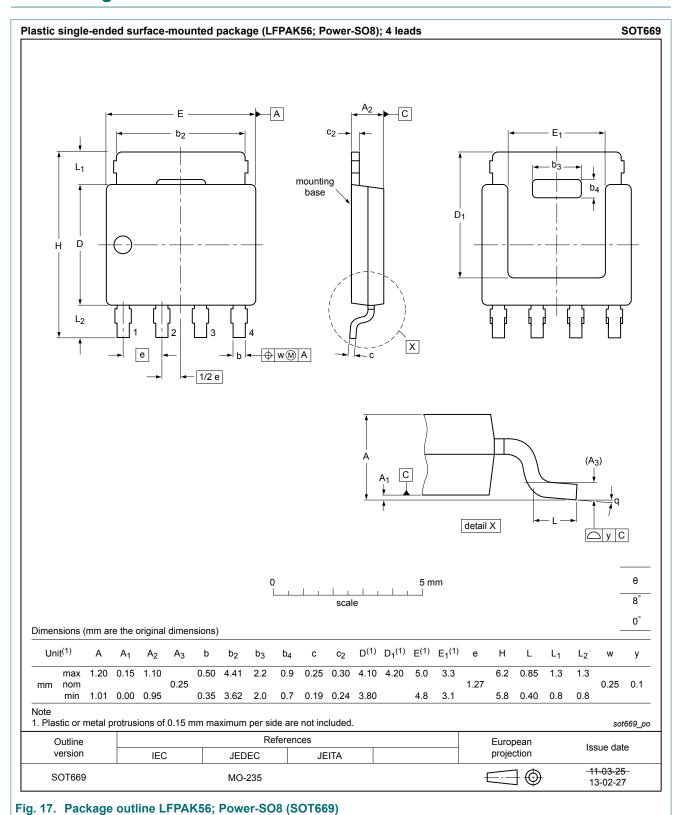


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
BUK6Y15-40P v.2	20180607	Product data sheet	-	BUK6Y15-40P v.1				
Modifications:	Package description	Package description updated.						
BUK6Y15-40P v.1	20180309	Product data sheet	-	-				

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BUK6Y15-40P

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